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# SN74CB3Q3125 Quadruple FET Bus Switch 2.5-V/3.3-V Low-Voltage, High-Bandwidth Bus Switch 

## 1 Features

- High-Bandwidth Data Path (up to $500 \mathrm{MHz}^{(1)}$ )
- 5-V Tolerant I/Os With Device Powered Up or Powered Down
- Low and Flat ON-State Resistance ( $r_{\text {on }}$ ) Characteristics Over Operating Range ( $r_{\text {on }}=3 \Omega$ Typ)
- Rail-to-Rail Switching on Data I/O Ports
- 0-V to 5-V Switching With 3.3-V $\mathrm{V}_{\mathrm{CC}}$
- 0-V to 3.3-V Switching With 2.5-V $V_{C C}$
- Bidirectional Data Flow With Near-Zero Propagation Delay
- Low Input and Output Capacitance Minimizes Loading and Signal Distortion
( $\mathrm{C}_{\mathrm{io}(\text { OFF })}=4 \mathrm{pF}$ Typ)
- Fast Switching Frequency ( $\mathrm{f} \overline{\mathrm{OE}}=20 \mathrm{MHz}$ Max)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption ( $\mathrm{I}_{\mathrm{CC}}=0.3 \mathrm{~mA}$ Typ)
- $\mathrm{V}_{\mathrm{CC}}$ Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0-V to 5-V Signaling Levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V )
- Control Inputs Can Be Driven by TTL, 5-V, or 3.3-V CMOS Outputs
- $I_{\text {off }}$ Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
- 2000-V Human-Body Model (A114-B, Class II)
- 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: USB Interface, Differential Signal Interface, Bus Isolation, Low-Distortion Signal Gating
(1) For additional information regarding the performance characteristics of the CB3Q family, refer to the TI application report, CBT-C, CB3T, and CB3Q Signal-Switch Families (SCDA008).


## 2 Applications

- IP Phones: Wired and Wireless
- Optical Modules
- Optical Networking: Video Over Fiber and EPON
- Private Branch Exchange (PBX)
- WiMAX and Wireless Infrastructure Equipment


## 3 Description

The SN74CB3Q3125 device is a high-bandwidth FET bus switch that uses a charge pump to elevate the gate voltage of the pass transistor, thus providing a low and flat ON-state resistance ( $r_{\text {on }}$ ). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The SN74CB3Q3125 device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus.

Device Information ${ }^{(1)}$

| PART NUMBER | PACKAGE | BODY SIZE (NOM) |
| :---: | :--- | :--- |
| SN74CB3Q3125 | $\operatorname{VQFN}(14)$ | $3.50 \mathrm{~mm} \times 3.50 \mathrm{~mm}$ |
|  | $\operatorname{SSOP}(16)$ | $4.90 \mathrm{~mm} \times 3.90 \mathrm{~mm}$ |
|  | TSSOP $(16)$ | $5.00 \mathrm{~mm} \times 4.40 \mathrm{~mm}$ |
|  | TVSOP $(16)$ | $4.40 \mathrm{~mm} \times 3.60 \mathrm{~mm}$ |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## Logic Diagram (Positive Logic)



Pin numbers shown are for the DGV, PW, and RGY packages.

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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NOTE: Page numbers for previous revisions may differ from page numbers in the current version.
Changes from Revision B (March 2005) to Revision C Page

- Added Pin Functions table, ESD Ratings table, Thermal Information table, Detailed Description section, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section ..... 1
- Deleted Ordering Information table. ..... 1


## 5 Pin Configuration and Functions

DGV, PW Packages
14-Pin TVSOP, TSSOP
Top View


|  | DBQ Pack 16-Pin SS Top Vie | kage <br> SO <br> w |
| :---: | :---: | :---: |
| NC | $1 \cup_{16}$ | $\mathrm{V}_{\mathrm{Cc}}$ |
| 1 $\overline{O E}$ | 215 | ] $4 \overline{O E}$ |
| 1A | 314 | ] 4 A |
| 1B | 413 | ] 4 B |
| 2OE | 512 | ] $3 \overline{O E}$ |
| 2A | $6 \quad 11$ | 3A |
| 2B | 710 | 73 B |
| GND | 89 | NC |

Pin Functions

| PIN |  |  | I/O |  |
| :--- | :---: | :---: | :---: | :--- |
| NAME | DGV, PW, <br> RGY | DBQ |  |  |
| 1 $\overline{\mathrm{OE}}$ | 1 | 2 | I | Output Enable (Active Low) |
| 1A | 2 | 3 | I/O | Channel 1A I/O 1A |
| 1B | 3 | 4 | I/O | Channel 1B I/O 1B |
| $2 \overline{O E}$ | 4 | 5 | I | Output Enable (Active Low) |
| 2A | 5 | 6 | I/O | Channel 2A I/O 2A |
| 2B | 6 | 7 | I/O | Channel 2B I/O 2B |
| GND | 7 | 8 | - | Ground |
| 3B | 8 | 10 | I/O | Channel 3B I/O 3B |
| 3A | 9 | 11 | I/O | Channel 3A I/O 3B |
| 3 $\overline{O E}$ | 10 | 12 | I | Output Enable (Active Low) |
| 4B | 11 | 13 | I/O | Channel 4B I/O 4B |
| 4A | 12 | 14 | I/O | Channel 4A I/O 4B |
| $4 \overline{O E}$ | 13 | 15 | I | Output Enable (Active Low) |
| NC | - | 1,9 | - | No Connect |
| VCC | 14 | 16 | - | Power |

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ${ }^{(1)}$

|  |  |  | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Supply voltage |  | -0.5 | 4.6 | V |
| $\mathrm{V}_{\text {IN }}$ | Control input voltage ${ }^{(2)(3)}$ |  | -0.5 | 7 | V |
| $\mathrm{V}_{\text {I/O }}$ | Switch I/O voltage ${ }^{(2)(3)(4)}$ |  | -0.5 | 7 | V |
| $I_{\text {I/K }}$ | Control input clamp current | $\mathrm{V}_{\text {IN }}<0$ |  | -50 | mA |
| $\mathrm{I}_{\text {I/OK }}$ | I/O port clamp current | $\mathrm{V}_{1 / \mathrm{O}}<0$ |  | -50 | mA |
| $\mathrm{I}_{1 \mathrm{O}} \quad$ ON-state switch current ${ }^{(5)}$ | ON-state switch current ${ }^{(5)}$ |  |  | $\pm 64$ | mA |
| Continuous current through $\mathrm{V}_{\text {cC }}$ or GND |  |  |  | $\pm 100$ | mA |
| $\mathrm{T}_{\mathrm{J}}$ | Junction temperature |  |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature |  | -65 | 150 |  |

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground, unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) $V_{I}$ and $V_{O}$ are used to denote specific conditions for $V_{I / O}$.
(5) $I_{I}$ and $I_{O}$ are used to denote specific conditions for $I_{/ / O}$.

### 6.2 ESD Ratings

|  |  | VALUE | UNIT |
| :---: | :---: | :---: | :---: |
|  | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ${ }^{(1)}$ | +2000 |  |
| $\mathrm{V}_{(\text {ESD })}$ Electrostatic discharge | Charged-device model (CDM), per JEDEC specification JESD22C101 ${ }^{(2)}$ | +1000 | V |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) ${ }^{(1)}$

|  |  | MIN | MAX | UNIT |  |
| :--- | :--- | :--- | ---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Supply voltage | 2.3 | 3.6 | V |  |
| $\mathrm{~V}_{\mathrm{IH}}$ | High-level control input voltage | $\mathrm{V}_{\mathrm{CC}}=2.3 \mathrm{~V}$ to 2.7 V | 1.7 | 5.5 | V |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=2.7 \mathrm{~V}$ to 3.6 V | 2 | 5.5 |  |
| $\mathrm{~V}_{\mathrm{IL}}$ | Low-level control input voltage | $\mathrm{V}_{\mathrm{CC}}=2.3 \mathrm{~V}$ to 2.7 V | 0 | 0.7 | V |
|  | $\mathrm{~V}_{\mathrm{CC}}=2.7 \mathrm{~V}$ to 3.6 V | 0 | 0.8 |  |  |
| $\mathrm{~V}_{\mathrm{I} / \mathrm{O}}$ | Data input and output voltage |  | 0 | 5.5 | V |
| $\mathrm{~T}_{\mathrm{A}}$ | Operating free-air temperature | -40 | 85 | ${ }^{\circ} \mathrm{C}$ |  |

(1) All unused control inputs of the device must be held at $\mathrm{V}_{\mathrm{Cc}}$ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs (SCBA004).

### 6.4 Thermal Information

| THERMAL METRIC ${ }^{(1)}$ |  | SN74CB3Q3257 |  |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | $\begin{aligned} & \hline \text { DBQ } \\ & \text { (SSOP) } \end{aligned}$ | DGV (TVSOP) | PW (TSSOP) | RGY (VQFN) |  |
|  |  | 16 PINS | 14 PINS | 14 PINS | 14 PINS |  |
| $\mathrm{R}_{\text {өJA }}$ | Junction-to-ambient thermal resistance | 90 | 127 | 113 | 47 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted) ${ }^{(1)}$

| PARAMETER |  | TEST CONDITIONS |  |  | MIN | TYP ${ }^{(2)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{IK}}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}$, | $\mathrm{I}_{\mathrm{I}}=-18 \mathrm{~mA}$ |  |  |  | -1.8 | V |
| $\mathrm{I}_{\mathrm{N}}$ | Control inputs | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | $\mathrm{V}_{\mathrm{IN}}=0$ to 5.5 V |  |  |  | $\pm 1$ | $\mu \mathrm{A}$ |
| $\mathrm{loz}^{(3)}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}$, | $\begin{aligned} & \mathrm{V}_{\mathrm{O}}=0 \text { to } 5.5 \mathrm{~V}, \\ & \mathrm{~V}_{1}=0, \end{aligned}$ | Switch OFF, $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND}$ |  |  | $\pm 1$ | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\text {off }}$ |  | $\mathrm{V}_{\mathrm{CC}}=0$, | $\mathrm{V}_{\mathrm{O}}=0$ to 5.5 V , | $\mathrm{V}_{1}=0$ |  |  | 1 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{Cc}}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}$, | $I_{1 / O}=0,$ <br> Switch ON or OFF, | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {CC }}$ or GND |  | 0.3 | 1 | mA |
| $\Delta \mathrm{lCC}^{(4)}$ | Control inputs | $\mathrm{V}_{C C}=3.6 \mathrm{~V}$, | One input at 3 V , | Other inputs at $\mathrm{V}_{\mathrm{CC}}$ or GND |  |  | 30 | $\mu \mathrm{A}$ |
| $I_{C C D}{ }^{(5)}$ | Per control input | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}, \quad \mathrm{~A}$ and B ports open, Control input switching at $50 \%$ duty cycle |  |  |  | 0.04 | 0.2 | $\begin{aligned} & \mathrm{mA} / \\ & \mathrm{MHz} \end{aligned}$ |
|  | Control inputs | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, | $\mathrm{V}_{\text {IN }}=5.5 \mathrm{~V}, 3.3 \mathrm{~V}$, or 0 |  |  | 2.5 | 3.5 | pF |
| $\mathrm{C}_{\text {io(OFF) }}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, | Switch OFF, <br> $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or GND , | $\mathrm{V}_{1 / \mathrm{O}}=5.5 \mathrm{~V}, 3.3 \mathrm{~V}$, or 0 |  | 4 | 5 | pF |
| $\mathrm{C}_{\mathrm{io}(\mathrm{ON})}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, | Switch ON, $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND} \text {, }$ | $\mathrm{V}_{1 / \mathrm{O}}=5.5 \mathrm{~V}, 3.3 \mathrm{~V}$, or 0 |  | 8 | 10 | pF |
| $\mathrm{r}_{\text {on }}{ }^{(6)}$ |  | $\begin{aligned} & V_{C C}=2.3 \mathrm{~V}, \\ & T Y P \text { at } V_{C C}=2.5 \mathrm{~V} \end{aligned}$ | $\mathrm{V}_{1}=0$, | $\mathrm{l}_{0}=30 \mathrm{~mA}$ |  | 4 | 8 | $\Omega$ |
|  |  |  | $\mathrm{V}_{1}=1.7 \mathrm{~V}$, | $\mathrm{l}_{\mathrm{O}}=-15 \mathrm{~mA}$ |  | 4 | 9 |  |
|  |  | $\mathrm{V}_{\mathrm{CC}}=3 \mathrm{~V}$ | $\mathrm{V}_{1}=0$, | $\mathrm{l}_{0}=30 \mathrm{~mA}$ |  | 4 | 6 |  |
|  |  |  | $\mathrm{V}_{1}=2.4 \mathrm{~V}$, | $\mathrm{l}_{\mathrm{O}}=-15 \mathrm{~mA}$ |  | 4 | 8 |  |

(1) $\mathrm{V}_{\mathbb{I N}}$ and $\mathrm{I}_{\mathbb{N}}$ refer to control inputs. $\mathrm{V}_{\mathrm{V}}, \mathrm{V}_{\mathrm{O}}, \mathrm{I}_{\mathrm{I}}$, and $\mathrm{I}_{\mathrm{O}}$ refer to data pins.
(2) All typical values are at $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$ (unless otherwise noted), $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$.
(3) For I/O ports, the parameter $\mathrm{I}_{\mathrm{Oz}}$ includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than $\mathrm{V}_{C C}$ or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see Figure 2).
(6) Measured by the voltage drop between the $A$ and $B$ terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two ( A or B ) terminals.

### 6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

| PARAMETER | FROM (INPUT) | $\begin{gathered} \text { TO } \\ \text { (OUTPUT) } \end{gathered}$ | $\mathrm{V}_{\mathrm{CC}}=2.5 \mathrm{~V} \pm 0.2 \mathrm{~V}$ |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN | MAX | MIN | MAX |  |
| $\mathrm{f} \overline{\mathrm{EE}}^{(1)}$ | $\overline{\mathrm{OE}}$ | A or B |  | 10 |  | 20 | MHz |
| $\mathrm{tpd}^{\text {(2) }}$ | A or B | $B$ or $A$ |  | 0.12 |  | 0.2 | ns |
| $\mathrm{t}_{\mathrm{en}}$ | $\overline{\mathrm{OE}}$ | A or B | 1.5 | 6.7 | 1.5 | 6.6 | ns |
| $\mathrm{t}_{\text {dis }}$ | $\overline{\mathrm{OE}}$ | A or B | 1 | 4.6 | 1 | 5.3 | ns |

(1) Maximum switching frequency for control input $\left(V_{O}>V_{C C}, V_{I}=5 V, R_{L} \geq 1 M \Omega, C_{L}=0\right)$
(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

### 6.7 Typical Characteristics

At $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ and $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$, unless otherwise noted.


Figure 1. Typical On-State Resistance vs Input Voltage

$A$ and $B$ Ports Open
Figure 2. Typical Supply Current vs OE Switching Frequency

## 7 Parameter Measurement Information



| TEST | $\mathrm{V}_{\mathrm{CC}}$ | S 1 | $\mathrm{R}_{\mathrm{L}}$ | $\mathrm{V}_{\mathrm{I}}$ | $\mathrm{C}_{\mathrm{L}}$ | $\mathrm{V}_{\Delta}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{pd}(\mathrm{s})}$ | $2.5 \mathrm{~V} \pm 0.2 \mathrm{~V}$ | Open | $500 \Omega$ | $\mathrm{~V}_{\mathrm{CC}}$ or GND | 30 pF |  |
|  | $3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | Open | $500 \Omega$ | $\mathrm{~V}_{\mathrm{CC}}$ or GND | 50 pF |  |
| $\mathrm{t}_{\mathrm{PLZ}} / \mathrm{t}_{\mathrm{PZL}}$ | $2.5 \mathrm{~V} \pm 0.2 \mathrm{~V}$ | $2 \times \mathrm{V}_{\mathrm{CC}}$ | $500 \Omega$ | GND | 30 pF | 0.15 V |
|  | $3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | $2 \times \mathrm{V}_{\mathrm{CC}}$ | $500 \Omega$ | GND | 50 pF | 0.3 V |
| $\mathrm{t}_{\mathrm{PHZ}} / \mathrm{t}_{\mathrm{PZH}}$ | $2.5 \mathrm{~V} \pm 0.2 \mathrm{~V}$ | GND | $500 \Omega$ | $\mathrm{~V}_{\mathrm{CC}}$ | 30 pF | 0.15 V |
|  | $3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | GND | $500 \Omega$ | $\mathrm{~V}_{\mathrm{CC}}$ | 50 pF | 0.3 V |


A. $C_{L}$ includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: $\mathrm{PRR} \leq 10 \mathrm{MHz}, \mathrm{Z}_{\mathrm{O}}=50 \Omega, \mathrm{t}_{\mathrm{r}} \leq 2.5 \mathrm{~ns}$, $\mathrm{t}_{\mathrm{f}} \leq 2.5 \mathrm{~ns}$.
D. The outputs are measured one at a time, with one transition per measurement.
E. $\quad t_{P L Z}$ and $t_{P H Z}$ are the same as $t_{\text {dis }}$.
F. $t_{\text {PZL }}$ and $t_{\text {PZH }}$ are the same as ten.
G. $\quad t_{P L H}$ and $t_{\text {PHL }}$ are the same as $t_{p d(s)}$. The $t_{p d}$ propagation delay is the calculated RC time constant of the typical ONstate resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
H. All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

## 8 Detailed Description

### 8.1 Overview

The SN74CB3Q3125 device is a high-bandwidth FET bus switch utilizing a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance ( $r_{\text {on }}$ ). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The SN74CB3Q3125 device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3125 device provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.
The SN74CB3Q3125 device is organized as four 1-bit bus switches with separate output-enable (1 $\overline{\mathrm{OE}}, 2 \overline{\mathrm{OE}}$, 3 $\overline{O E}, 4 \overline{\mathrm{OE}})$ inputs. It can be used as four 1 -bit bus switches or as one 4 -bit bus switch. When OE is low, the associated 1-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{\mathrm{OE}}$ is high, the associated 1-bit bus switch is OFF, and a high-impedance state exists between the $A$ and $B$ ports.

This device is fully specified for partial-power-down applications using $\mathrm{I}_{\text {off }}$. The $\mathrm{I}_{\text {off }}$ circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.
To ensure the high-impedance state during power up or power down, $\overline{\mathrm{OE}}$ should be tied to $\mathrm{V}_{\mathrm{CC}}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.


Figure 4. Simplified Schematic, Each FET Switch (SW)

### 8.2 Functional Block Diagram



### 8.3 Feature Description

The SN74CB3Q3125 device has a high-bandwidth data path (up to 500 MHz ) and has $5-\mathrm{V}$ tolerant I/Os with the device powered up or powered down. It also has low and flat ON -state resistance ( $\mathrm{r}_{\text {on }}$ ) characteristics over operating range ( $\mathrm{r}_{\text {on }}=4-\Omega$ Typ).
The SN74CB3Q3125 device has rail-to-rail switching on data I/O ports for $0-\mathrm{V}$ to $5-\mathrm{V}$ switching with $3.3-\mathrm{V} \mathrm{V}_{\mathrm{cc}}$ and $0-\mathrm{V}$ to $3.3-\mathrm{V}$ switching with $2.5-\mathrm{V} \mathrm{V}_{\mathrm{cc}}$ as well as bidirectional data flow with near-zero propagation delay and low input/output capacitance that minimizes loading and signal distortion ( $\mathrm{C}_{\mathrm{io}(\mathrm{OFF})}=3.5-\mathrm{pF}$ Typ).
The SN74CB3Q3125 device also provides a fast switching frequency ( $f \mathrm{fE}=20-\mathrm{MHz} \mathrm{Max}$ ) with data and control inputs that provide undershoot clamp diodes as well as low power consumption ( $\mathrm{I}_{\mathrm{cc}}=0.6-\mathrm{mA} \mathrm{Typ}$ ).
The $\mathrm{V}_{\mathrm{CC}}$ operating range is from 2.3 V to 3.6 V and the data $\mathrm{I} / \mathrm{O}$ s support $0-\mathrm{V}$ to $5-\mathrm{V}$ signal levels of ( $0.8 \mathrm{~V}, 1.2 \mathrm{~V}, 1.5 \mathrm{~V}, 1.8 \mathrm{~V}, 2.5 \mathrm{~V}, 3.3 \mathrm{~V}, 5 \mathrm{~V}$ ).
The control inputs can be driven by TTL or $5-\mathrm{V}$ or $3.3-\mathrm{V}$ CMOS outputs, and $\mathrm{I}_{\text {off }}$ supports partial-power-down mode operation.

### 8.4 Device Functional Modes

Table 1 lists the functional modes for the SN74CB3Q3125 device.
Table 1. Function Table

| INPUT <br> $\overline{\mathrm{OE}}$ | INPUT/OUTPUT <br> $\mathbf{A}$ | FUNCTION |
| :---: | :---: | :---: |
| L | B | A port = B port |
| H | Z | Disconnect |

## 9 Application and Implementation

## NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The SN74CB3Q3125 device can be used to control up to four channels simultaneously.

### 9.2 Typical Application

The application shown in Figure 5 is a 4-bit bus being controlled. The $\overline{\mathrm{OE}}$ pins are used to control the chip from the bus controller. This is a very generic example and can apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.


Pin numbers for DGV, PW, RGY packages
only

Figure 5. Typical Application of the SN74CB3Q3257

### 9.2.1 Design Requirements

The $0.1-\mu \mathrm{F}$ capacitor must be placed as close as possible to the SN74CB3Q3257 device.

## Typical Application (continued)

### 9.2.2 Detailed Design Procedure

1. Recommended input conditions:

- For specified high and low levels, see $\mathrm{V}_{\mathrm{IH}}$ and $\mathrm{V}_{\mathrm{IL}}$ in Recommended Operating Conditions
- Inputs and outputs are overvoltage tolerant, which slows them to go as high as 5.5 V at any valid $\mathrm{V}_{\mathrm{CC}}$

2. Recommended output conditions:

- Load currents must not exceed $\pm 64 \mathrm{~mA}$ per channel

3. Frequency selection criterion:

- Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in Layout


### 9.2.3 Application Curve



Figure 6. Propagation Delay ( $\mathrm{t}_{\mathrm{pd}}$ ) Simulation Result at $\mathrm{V}_{\mathrm{cc}}=3.3 \mathrm{~V}$

## 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the Absolute Maximum Ratings table.
Each $\mathrm{V}_{\mathrm{CC}}$ terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a $0.1-\mu \mathrm{F}$ bypass capacitor is recommended. If multiple pins are labeled $\mathrm{V}_{\mathrm{Cc}}$, then a $0.01-\mu \mathrm{F}$ or $0.022-\mu \mathrm{F}$ capacitor is recommended for each $\mathrm{V}_{C C}$ because the $\mathrm{V}_{C C}$ pins are tied together internally. For devices with dualsupply pins operating at different voltages, for example $\mathrm{V}_{\mathrm{CC}}$ and $\mathrm{V}_{\mathrm{DD}}$, a $0.1-\mu \mathrm{F}$ bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of $0.1 \mu \mathrm{~F}$ and $1 \mu \mathrm{~F}$ are commonly used in parallel. The bypass capacitor must be installed as close to the power terminal as possible for best results.

## 11 Layout

### 11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a $90^{\circ}$ angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace, which results in the reflection. Not all PCB traces can be straight; therefore, some traces must turn corners. Figure 7 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

### 11.2 Layout Example

WORST


BETTER


W

BEST


Figure 7. Trace Example

## 12 Device and Documentation Support

### 12.1 Documentation Support

### 12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030


### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.
TI E2ETM Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.
Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 12.3 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

### 12.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam
during storage or handling to prevent electrostatic damage to the MOS gates.

### 12.5 Glossary

SLYZ022 - TI Glossary.
This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

| Orderable Device | Status <br> (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan <br> (2) | Lead finish/ Ball material <br> (6) | MSL Peak Temp <br> (3) | Op Temp ( ${ }^{\circ} \mathrm{C}$ ) | Device Marking <br> (4/5) | Samples |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 74CB3Q3125DBQRE4 | ACTIVE | SSOP | DBQ | 16 | 2500 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125DBQR | ACTIVE | SSOP | DBQ | 16 | 2500 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125DGVR | ACTIVE | TVSOP | DGV | 14 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125PW | ACTIVE | TSSOP | PW | 14 | 90 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125PWR | ACTIVE | TSSOP | PW | 14 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125PWRE4 | ACTIVE | TSSOP | PW | 14 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125PWRG4 | ACTIVE | TSSOP | PW | 14 | 2000 | RoHS \& Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BU125 | Samples |
| SN74CB3Q3125RGYR | ACTIVE | VQFN | RGY | 14 | 3000 | RoHS \& Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BU125 | Samples |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
${ }^{(2)}$ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.
${ }^{(3)}$ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
${ }^{(4)}$ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
${ }^{(5)}$ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
${ }^{(6)}$ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION


*All dimensions are nominal

| Device | Package <br> Type | Package <br> Drawing | Pins | SPQ | Reel <br> Diameter <br> $(\mathbf{m m})$ | Reel <br> Width <br> $\mathbf{W 1}(\mathbf{m m})$ | A0 <br> $(\mathbf{m m})$ | B0 <br> $(\mathbf{m m})$ | K0 <br> $(\mathbf{m m})$ | P1 <br> $(\mathbf{m m})$ | W <br> $(\mathbf{m m})$ | Pin1 <br> Quadrant |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q3125DBQR | SSOP | DBQ | 16 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| SN74CB3Q3125DGVR | TVSOP | DGV | 14 | 2000 | 330.0 | 12.4 | 6.8 | 4.0 | 1.6 | 8.0 | 12.0 | Q1 |
| SN74CB3Q3125PWR | TSSOP | PW | 14 | 2000 | 330.0 | 12.4 | 6.9 | 5.6 | 1.6 | 8.0 | 12.0 | Q1 |
| SN74CB3Q3125RGYR | VQFN | RGY | 14 | 3000 | 330.0 | 12.4 | 3.75 | 3.75 | 1.15 | 8.0 | 12.0 | Q1 |

PACKAGE MATERIALS INFORMATION

*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q3125DBQR | SSOP | DBQ | 16 | 2500 | 340.5 | 338.1 | 20.6 |
| SN74CB3Q3125DGVR | TVSOP | DGV | 14 | 2000 | 367.0 | 367.0 | 35.0 |
| SN74CB3Q3125PWR | TSSOP | PW | 14 | 2000 | 367.0 | 367.0 | 35.0 |
| SN74CB3Q3125RGYR | VQFN | RGY | 14 | 3000 | 367.0 | 367.0 | 35.0 |

## TUBE



B - Alignment groove width
*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W $(\mathbf{m m})$ | T $(\boldsymbol{\mu m})$ | B (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN74CB3Q3125PW | PW | TSSOP | 14 | 90 | 530 | 10.2 | 3600 | 3.5 |



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No-Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated.
The Pin 1 identifiers are either a molded, marked, or metal feature.
G. Package complies to JEDEC MO-241 variation BA.
RGY (S-PVQFN-N14) PLASTIC QUAD FLATPACK NO-LEAD

## THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).
For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.


Bottom View

Exposed Thermal Pad Dimensions

NOTE: All linear dimensions are in millimeters


NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com [http://www.ti.com](http://www.ti.com).
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.


| PIM ** | $\mathbf{1 4}$ | $\mathbf{1 6}$ | $\mathbf{2 0}$ | $\mathbf{2 4}$ | $\mathbf{3 8}$ | $\mathbf{4 8}$ | $\mathbf{5 6}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A MAX | 3,70 | 3,70 | 5,10 | 5,10 | 7,90 | 9,80 | 11,40 |
| A MIN | 3,50 | 3,50 | 4,90 | 4,90 | 7,70 | 9,60 | 11,20 |

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: $24 / 48$ Pins - MO-153

14/16/20/56 Pins - MO-194


NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
(D) Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO-153


NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.


## NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.


SOLDER MASK DETAILS

## NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE
BASED ON . 005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

NOTES: (continued)
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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